Ĺ	Hits	Search Text	DB	Time stamp
Number				
10	79354	mosfet (metal near oxide near	USPAT;	2004/06/01
		semiconductor near field-effect near	US-PGPUB;	12:33
		transistor) (metal near oxide near	EPO; JPO;	
		semiconductor near field-effect near	DERWENT;	
		transistor) (mos with fet)	IBM TDB	
11	1131388	trench\$2 recess\$2 trough\$2	USPĀT;	2004/06/01
		•	US-PGPUB;	12:34
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
12	36515	body adj2 (region area)	USPAT;	2004/06/01
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	12:34
			EPO; JPO;]
			DERWENT;	
			IBM TDB	1
13	54383	epitaxial near2 (layer film)	USPAT;	2004/06/01
			US-PGPUB;	12:35
			EPO; JPO;	1
			DERWENT;	1
			IBM TDB	
17	57149	(polycrystal\$4 poly-crystal\$4) with	USPAT;	2004/06/01
		silicon	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
18	306	(mosfet (metal near oxide near	USPAT;	2004/06/01
		semiconductor near field-effect near	US-PGPUB;	12:45
		transistor) (metal near oxide near	EPO; JPO;	
		semiconductor near field-effect near	DERWENT;	
		transistor) (mos with fet)) and (trench\$2	IBM TDB	
		recess\$2 trough\$2) and (body adj2 (region		
	1	area)) and (epitaxial near2 (layer film))		
		and ((polycrystal\$4 poly-crystal\$4) with		
		silicon)		